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This effect is called **well proximity effect**. BSIM4 considers the influence of **well proximity effect** on **threshold voltage**, mobility, and body effect. ...

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which leads to **threshold voltage** increase for devices close to the well edge.

Well proximity effect on NFET $\Delta V_{th} \approx +50\text{mV}$ and PFET $\Delta V_{th} \approx +20\text{mV}$...

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... with using ion implantation to form wells is the **well proximity effect**, ...

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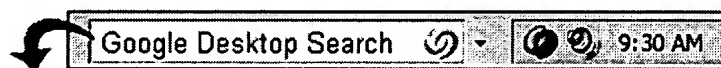
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Semiconductor Manufacturing, 2005. ISSM 2005, IEEE International Symposium
13-15 Sept. 2005 Page(s):193 - 196
Digital Object Identifier 10.1109/ISSM.2005.1513333
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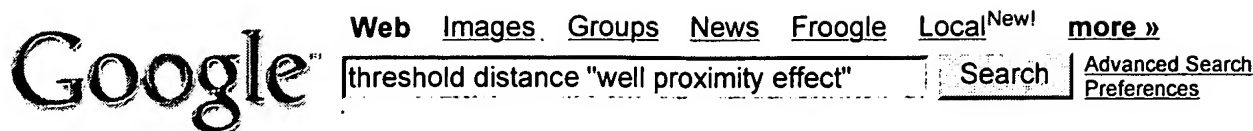
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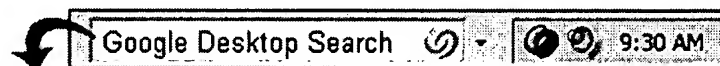
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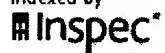
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